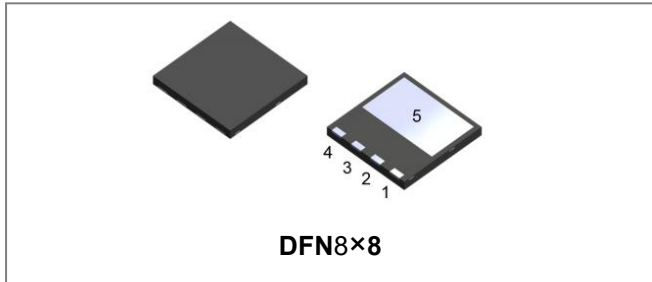


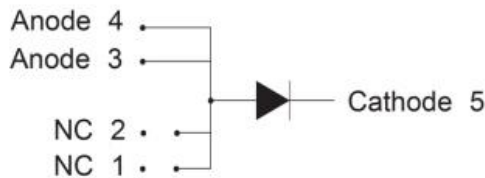
## S3D06065L 650V SiC POWER SCHOTTKY RECTIFIER



### Description

S3D06065L is a SiC Schottky rectifier packaged in DFN8x8 case. The device is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D06065L is ideal for energy sensitive, high frequency applications in challenging environments.

### Circuit Diagram



### Features

- 175°C T<sub>J</sub> operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- “-A” is an AEC-Q101 qualified device
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

### Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

### Maximum Ratings

| Characteristics                             | Symbol              | Condition                                    | Max. | Units |
|---|---------------------|--|------|-------|
| Peak Repetitive Reverse Voltage             | V <sub>RRM</sub>    | -  | 650  | V     |
| Working Peak Reverse Voltage                | V <sub>RWM</sub>    |  |      |       |
| DC Blocking Voltage                         | V <sub>DC</sub>     |  |      |       |
| Average Rectified Forward Current           | I <sub>F(AV)1</sub> | T <sub>C</sub> =25°C                         | 24   | A     |
|   | I <sub>F(AV)2</sub> | T <sub>C</sub> =136°C                        | 9    | A     |
|   | I <sub>F(AV)3</sub> | T <sub>C</sub> =157°C                        | 6    | A     |
| Repetitive Peak Forward Surge Current       | I <sub>FRM1</sub>   | 10ms, Half Sine pulse, T <sub>C</sub> =25°C  | 30   | A     |
|   | I <sub>FRM2</sub>   | 10ms, Half Sine pulse, T <sub>C</sub> =110°C | 20   | A     |
| Peak One Cycle Non-Repetitive Surge Current | I <sub>FSM1</sub>   | 10ms, Half Sine pulse, T <sub>C</sub> =25°C  | 70   | A     |
|   | I <sub>FSM2</sub>   | 10ms, Half Sine pulse, T <sub>C</sub> =110°C | 48   | A     |
| Non-Repetitive Peak Forward Surge Current   | I <sub>F,Max1</sub> | 10µs. Pulse, T <sub>C</sub> =25°C            | 600  | A     |
|   | I <sub>F,Max2</sub> | 10µs. Pulse, T <sub>C</sub> =110°C           | 500  | A     |
| Power Dissipation                           | P <sub>tot1</sub>   | T <sub>C</sub> =25°C                         | 103  | W     |
|   | P <sub>tot2</sub>   | T <sub>C</sub> =110°C                        | 45   | W     |

**Electrical Characteristics:**

| Characteristics           | Symbol          | Condition   | Typ. | Max. | Units |
|---------------------------|-----------------|---|------|------|-------|
| Forward Voltage Drop*     | V <sub>F1</sub> | @ 6A, Pulse, T <sub>J</sub> = 25 °C   | 1.5  | 1.7  | V     |
|                           | V <sub>F2</sub> | @ 6A, Pulse, T <sub>J</sub> = 175 °C  | 1.9  | 2.4  | V     |
| Reverse Current*          | I <sub>R1</sub> | @V <sub>R</sub> = rated V <sub>R</sub><br>T <sub>J</sub> = 25 °C                        | 0.03 | 3    | uA    |
|                           | I <sub>R2</sub> | @V <sub>R</sub> = rated V <sub>R</sub><br>T <sub>J</sub> = 175 °C                       | 0.6  | 25   | uA    |
| Junction Capacitance      | C <sub>T</sub>  | V <sub>R</sub> =0V, T <sub>J</sub> =25°C, f=1MHz  | 382  | -    | pF    |
| Reverse Recovery Charge   | Q <sub>c</sub>  | I <sub>F</sub> = 6A, di/dt =<br>200A/μs<br>V <sub>R</sub> = 400 V, T <sub>J</sub> =25°C | 23.8 | -    | nC    |
| Capacitance Stored Energy | E <sub>c</sub>  | V <sub>R</sub> = 400 V, T <sub>J</sub> =25°C  | 5.88 | -    | μJ    |

\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

| Characteristics                             | Symbol           | Condition    | Specification | Units |
|---|------------------|--------------|---------------|-------|
| Junction Temperature                        | T <sub>J</sub>   | -            | -55 to +175   | °C    |
| Storage Temperature                         | T <sub>stg</sub> | -            | -55 to +175   | °C    |
| Typical Thermal Resistance Junction to Case | R <sub>θJC</sub> | DC operation | 2.5           | °C/W  |

**Marking Diagram**


Where XXXXX is YYWWL

S3D = Device Type  
L = Package type  
06 = Forward Current (6A)  
065 = Reverse Voltage (650V)  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information**

| Device      | Package | Shipping  |
|-------------|---------|-----------|
| S3D06065L   | DFN 8×8 | 3000/Reel |
| S3D06065LTR | DFN 8×8 | 3000/Reel |

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - [sales@smc-diodes.com](mailto:sales@smc-diodes.com) •

**Ratings and Characteristics Curves**

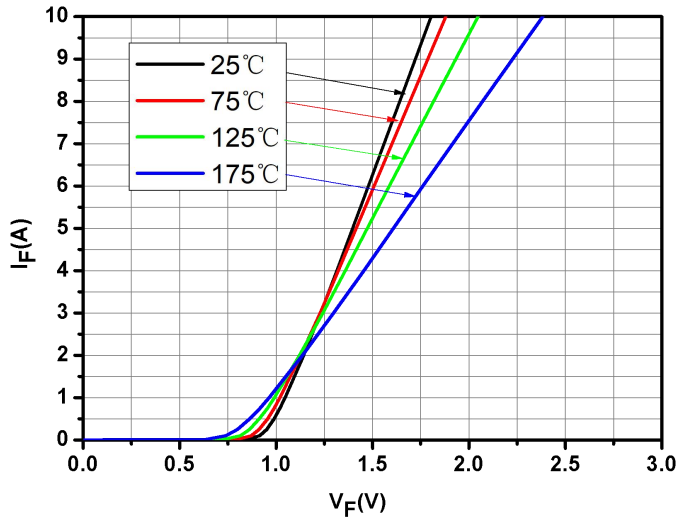


Fig.1-Typical Forward Voltage Characteristics

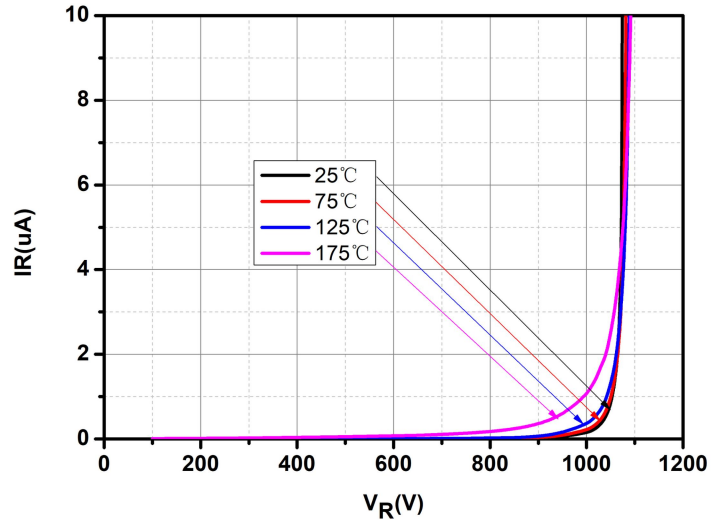


Fig.2-Typical Reverse Characteristics

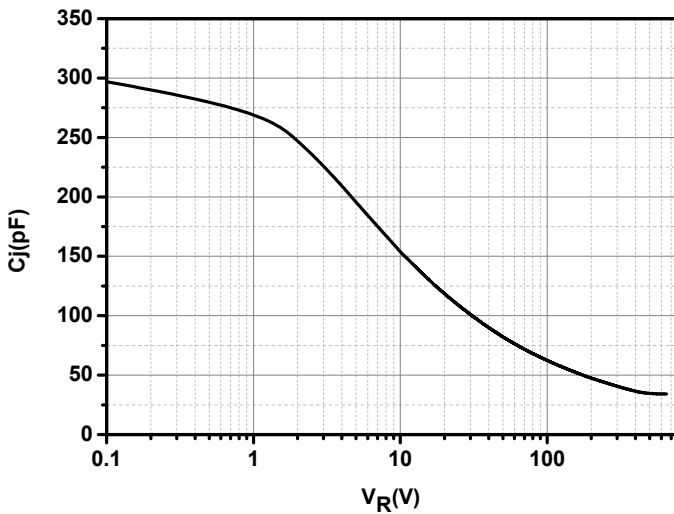


Fig.3-Capacitance vs. Reverse Voltage

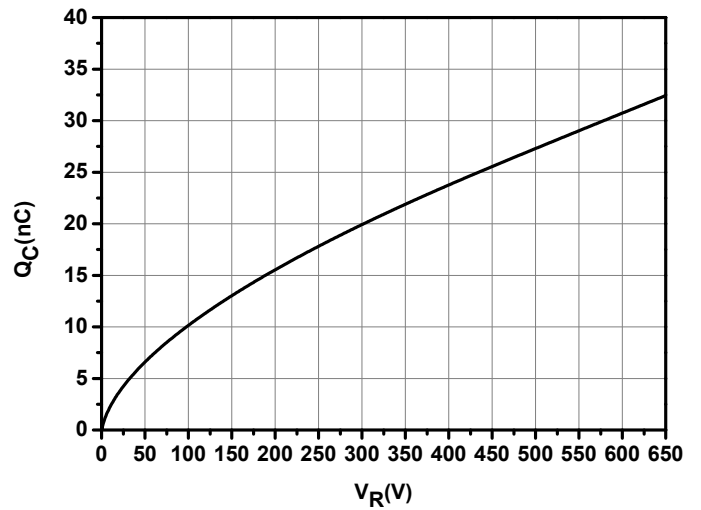


Fig.4-Total Capacitance Charge vs. Reverse Voltage

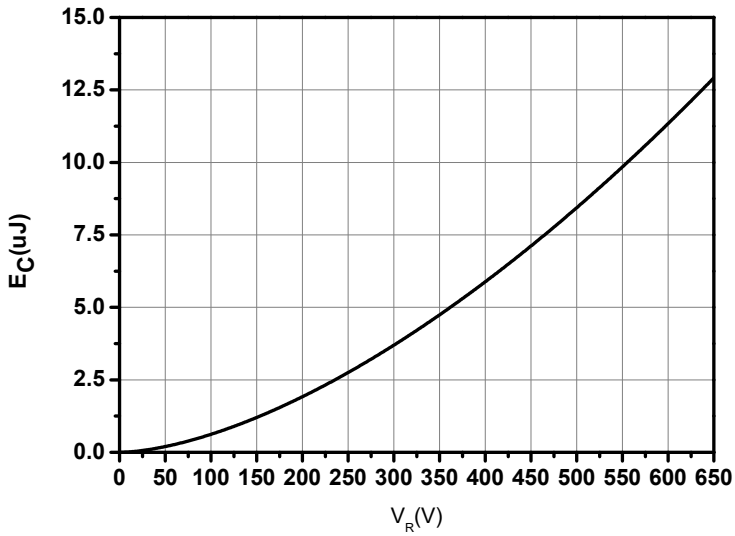


Fig.5-Capacitance Stored Energy

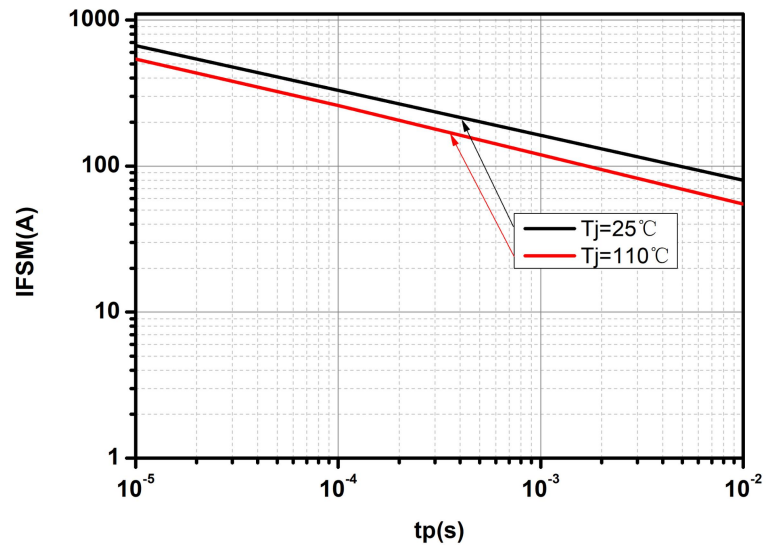


Fig.6-Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

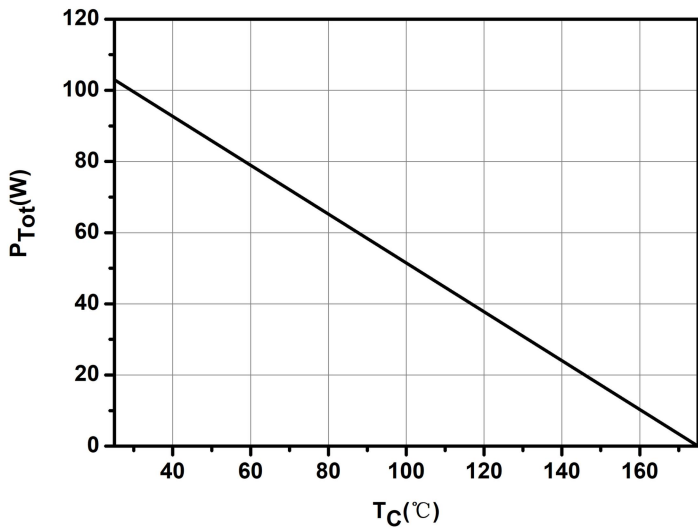


Fig.7-Power Derating

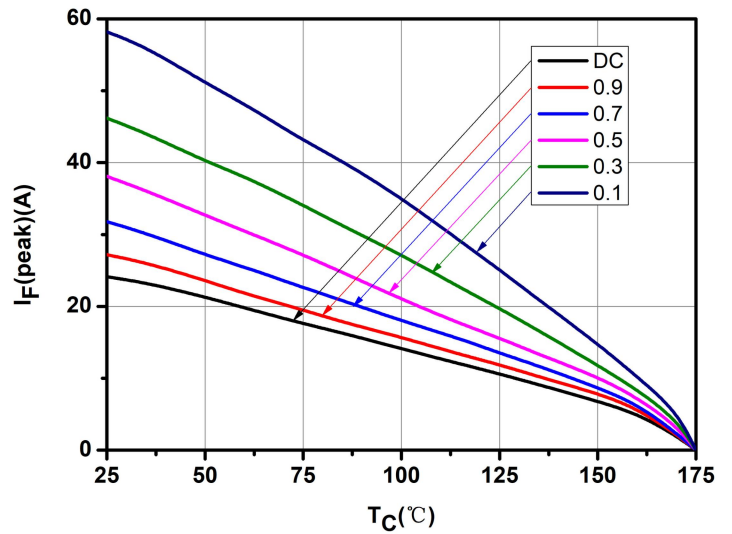
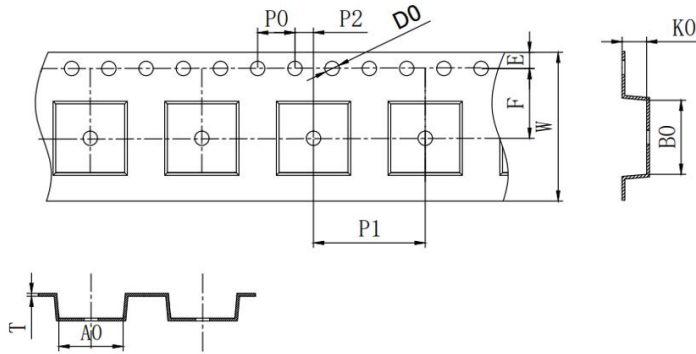


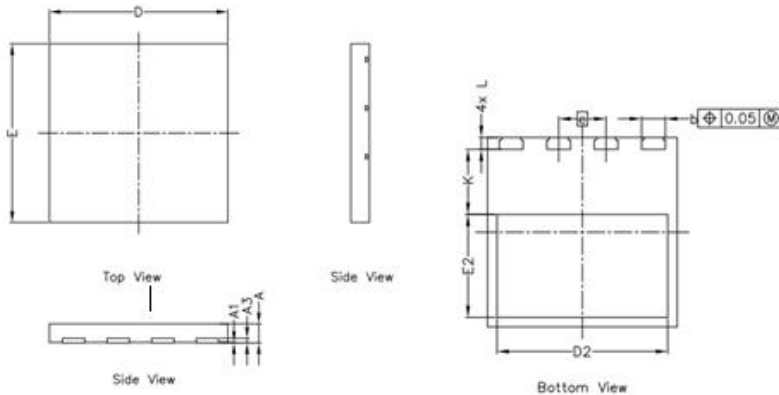
Fig.8-Current Derating

### Carrier Tape & Reel Specification DFN8x8



| SYMBOL | Millimeters |       |
|--------|-------------|-------|
|        | Min.        | Max.  |
| A0     | 8.30        | 8.50  |
| B0     | 8.40        | 8.60  |
| K0     | 1.20        | 1.40  |
| P0     | 3.90        | 4.10  |
| P1     | 11.90       | 12.10 |
| P2     | 1.95        | 2.05  |
| T      | 0.20        | 0.30  |
| E      | 1.65        | 1.85  |
| F      | 7.40        | 7.60  |
| D0     | 1.50        | 1.60  |
| D1     | 1.50        |       |
| W      | 15.70       | 16.30 |

### Mechanical Dimensions DFN8x8



| SYMBOL | Millimeters |       |
|--------|-------------|-------|
|        | Min.        | Max.  |
| A      | 0.800       | 0.900 |
| A1     | -           | 0.050 |
| A3     | 0.195       | 0.211 |
| D      | 7.900       | 8.100 |
| E      | 7.900       | 8.100 |
| e      | 2.00 BSC    |       |
| b      | 0.950       | 1.050 |
| D2     | 7.100       | 7.300 |
| E2     | 4.250       | 4.450 |
| L      | 0.400       | 0.600 |
| K      | 2.650       | 2.850 |



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